

ABSTRACT

A semiconductor treating device [(1)] includes treating chamber [(2)] connected to a common transportation chamber [(8)] and treating a substrate [(W)] to be treated. A gas supply system [(40)] for supplying system [(40)] for supplying a predetermined gas to each of the treating chambers [(2)] is attached to each chamber. The gas supply system [(40)] has a primary side connection unit [(23)] connected to the source of the predetermined gas and has a flow rate control unit [(2)]. The primary side connection unit [(23)] connected to the source of the predetermined gas and has a flow rate control unit [(2)]. The primary side connection unit [(23)] is placed on the lower side of the corresponding treating chamber [(2)]. The flow rate control unit [(2)] is placed on a gas line for supplying the gas from the primary side connection unit [(23)] to the corresponding treating chamber [(2)]. The flow rate control unit [(2)] is provided such that at least a part of it is superposed on the upper side of the primary side connection unit [(23)].